

MOSFET

Metal Oxide Semiconductor Field Effect Transistor

CoolMOS™ P6

600V CoolMOS™ P6 Power Transistor
IPx60R380P6

Data Sheet

Rev. 2.2
Final

1 Description

CoolMOS™ is a revolutionary technology for high voltage power MOSFETs, designed according to the superjunction (SJ) principle and pioneered by Infineon Technologies. CoolMOS™ P6 series combines the experience of the leading SJ MOSFET supplier with high class innovation. The offered devices provide all benefits of a fast switching SJ MOSFET while not sacrificing ease of use. Extremely low switching and conduction losses make switching applications even more efficient, more compact, lighter and cooler.

Features

- Increased MOSFET dv/dt ruggedness
- Extremely low losses due to very low FOM $R_{DS(on)} \cdot Q_g$ and E_{oss}
- Very high commutation ruggedness
- Easy to use/drive
- Pb-free plating, Halogen free mold compound
- Qualified for industrial grade applications according to JEDEC (J-STD20 and JESD22)

Applications

PFC stages, hard switching PWM stages and resonant switching stages for e.g. PC Silverbox, Adapter, LCD & PDP TV, Lighting, Server, Telecom and UPS.

Please note: For MOSFET paralleling the use of ferrite beads on the gate or separate totem poles is generally recommended.

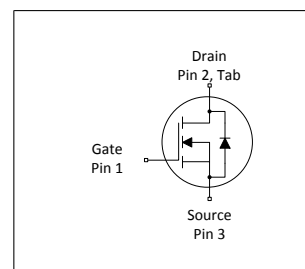
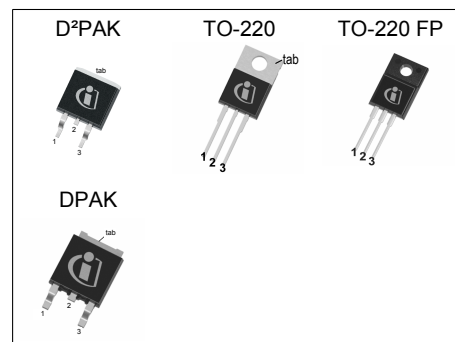


Table 1 Key Performance Parameters

Parameter	Value	Unit
$V_{DS} @ T_{j,max}$	650	V
$R_{DS(on),max}$	380	mΩ
$Q_{g,typ}$	19	nC
$I_{D,pulse}$	29	A
$E_{oss@400V}$	2.7	μJ
Body diode di/dt	500	A/μs

Type / Ordering Code	Package	Marking	Related Links
IPB60R380P6	PG-TO 263	6R380P6	see Appendix A
IPP60R380P6	PG-TO 220		
IPA60R380P6	PG-TO 220 FullPAK		
IPD60R380P6	PG-TO 252		

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2 Maximum ratings

at $T_j = 25^\circ\text{C}$, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current ¹⁾	I_D	-	-	10.6 6.7	A	$T_C=25^\circ\text{C}$ $T_C=100^\circ\text{C}$
Pulsed drain current ²⁾	$I_{D,pulse}$	-	-	29	A	$T_C=25^\circ\text{C}$
Avalanche energy, single pulse	E_{AS}	-	-	210	mJ	$I_D=1.8\text{A}$; $V_{DD}=50\text{V}$; see table 12
Avalanche energy, repetitive	E_{AR}	-	-	0.32	mJ	$I_D=1.8\text{A}$; $V_{DD}=50\text{V}$; see table 12
Avalanche current, repetitive	I_{AR}	-	-	1.8	A	-
MOSFET dv/dt ruggedness	dv/dt	-	-	100	V/ns	$V_{DS}=0\dots400\text{V}$
Gate source voltage (static)	V_{GS}	-20	-	20	V	static;
Gate source voltage (dynamic)	V_{GS}	-30	-	30	V	AC ($f>1\text{ Hz}$)
Power dissipation (Non FullPAK) TO-220, TO-252, TO-263	P_{tot}	-	-	83	W	$T_C=25^\circ\text{C}$
Power dissipation (FullPAK) TO-220FP	P_{tot}	-	-	31	W	$T_C=25^\circ\text{C}$
Storage temperature	T_{stg}	-55	-	150	$^\circ\text{C}$	-
Operating junction temperature	T_j	-55	-	150	$^\circ\text{C}$	-
Mounting torque (Non FullPAK) TO-220	-	-	-	60	Ncm	M3 and M3.5 screws
Mounting torque (FullPAK) TO-220FP	-	-	-	50	Ncm	M2.5 screws
Continuous diode forward current	I_S	-	-	9.2	A	$T_C=25^\circ\text{C}$
Diode pulse current ²⁾	$I_{S,pulse}$	-	-	29	A	$T_C=25^\circ\text{C}$
Reverse diode dv/dt ³⁾	dv/dt	-	-	15	V/ns	$V_{DS}=0\dots400\text{V}$, $I_{SD}\leq I_S$, $T_j=25^\circ\text{C}$ see table 10
Maximum diode commutation speed	di/dt	-	-	500	A/ μs	$V_{DS}=0\dots400\text{V}$, $I_{SD}\leq I_S$, $T_j=25^\circ\text{C}$ see table 10
Insulation withstand voltage for TO-220FP	V_{ISO}	-	-	2500	V	V_{rms} , $T_C=25^\circ\text{C}$, $t=1\text{min}$

¹⁾ Limited by $T_{j,max}$. Maximum duty cycle $D=0.75$

²⁾ Pulse width t_p limited by $T_{j,max}$

³⁾ Identical low side and high side switch with identical R_G

3 Thermal characteristics

Table 3 Thermal characteristics (Non FullPAK) TO-220

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	-	1.5	°C/W	-
Thermal resistance, junction - ambient	R_{thJA}	-	-	62	°C/W	leaded
Soldering temperature, wavesoldering only allowed at leads	T_{sold}	-	-	260	°C	1.6mm (0.063 in.) from case for 10s

Table 4 Thermal characteristics (FullPAK) TO-220FP

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	-	4	°C/W	-
Thermal resistance, junction - ambient	R_{thJA}	-	-	80	°C/W	leaded
Soldering temperature, wavesoldering only allowed at leads	T_{sold}	-	-	260	°C	1.6mm (0.063 in.) from case for 10s

Table 5 Thermal characteristics TO-252, TO-263

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	-	1.5	°C/W	-
Thermal resistance, junction - ambient	R_{thJA}	-	-	62	°C/W	device on PCB, minimal footprint
Thermal resistance, junction - ambient for SMD version	R_{thJA}	-	35	45	°C/W	Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm ² (one layer, 70µm thickness) copper area for drain connection and cooling. PCB is vertical without air stream cooling.
Soldering temperature, wave & reflow soldering allowed	T_{sold}	-	-	260	°C	reflow MSL1

4 Electrical characteristics

at $T_j=25^\circ\text{C}$, unless otherwise specified

Table 6 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	600	-	-	V	$V_{GS}=0\text{V}$, $I_D=1\text{mA}$
Gate threshold voltage	$V_{(GS)th}$	3.5	4.0	4.5	V	$V_{DS}=V_{GS}$, $I_D=0.32\text{mA}$
Zero gate voltage drain current	I_{DSS}	-	-	1	μA	$V_{DS}=600$, $V_{GS}=0\text{V}$, $T_j=25^\circ\text{C}$ $V_{DS}=600$, $V_{GS}=0\text{V}$, $T_j=150^\circ\text{C}$
Gate-source leakage current	I_{GSS}	-	-	100	nA	$V_{GS}=20\text{V}$, $V_{DS}=0\text{V}$
Drain-source on-state resistance	$R_{DS(on)}$	-	0.342 0.889	0.380 -	Ω	$V_{GS}=10\text{V}$, $I_D=3.8\text{A}$, $T_j=25^\circ\text{C}$ $V_{GS}=10\text{V}$, $I_D=3.8\text{A}$, $T_j=150^\circ\text{C}$
Gate resistance	R_G	-	7.8	-	Ω	$f=1\text{MHz}$, open drain

Table 7 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	C_{iss}	-	877	-	pF	$V_{GS}=0\text{V}$, $V_{DS}=100\text{V}$, $f=1\text{MHz}$
Output capacitance	C_{oss}	-	42	-	pF	$V_{GS}=0\text{V}$, $V_{DS}=100\text{V}$, $f=1\text{MHz}$
Effective output capacitance, energy related ¹⁾	$C_{o(er)}$	-	33	-	pF	$V_{GS}=0\text{V}$, $V_{DS}=0\dots400\text{V}$
Effective output capacitance, time related ²⁾	$C_{o(tr)}$	-	135	-	pF	$I_D=\text{constant}$, $V_{GS}=0\text{V}$, $V_{DS}=0\dots400\text{V}$
Turn-on delay time	$t_{d(on)}$	-	12	-	ns	$V_{DD}=400\text{V}$, $V_{GS}=13\text{V}$, $I_D=4.8\text{A}$, $R_G=3.4\Omega$; see table 11
Rise time	t_r	-	6	-	ns	$V_{DD}=400\text{V}$, $V_{GS}=13\text{V}$, $I_D=4.8\text{A}$, $R_G=3.4\Omega$; see table 11
Turn-off delay time	$t_{d(off)}$	-	33	-	ns	$V_{DD}=400\text{V}$, $V_{GS}=13\text{V}$, $I_D=4.8\text{A}$, $R_G=3.4\Omega$; see table 11
Fall time	t_f	-	7	-	ns	$V_{DD}=400\text{V}$, $V_{GS}=13\text{V}$, $I_D=4.8\text{A}$, $R_G=3.4\Omega$; see table 11

Table 8 Gate charge characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	5.4	-	nC	$V_{DD}=400\text{V}$, $I_D=4.8\text{A}$, $V_{GS}=0$ to 10V
Gate to drain charge	Q_{gd}	-	7	-	nC	$V_{DD}=400\text{V}$, $I_D=4.8\text{A}$, $V_{GS}=0$ to 10V
Gate charge total	Q_g	-	19	-	nC	$V_{DD}=400\text{V}$, $I_D=4.8\text{A}$, $V_{GS}=0$ to 10V
Gate plateau voltage	$V_{plateau}$	-	6.1	-	V	$V_{DD}=400\text{V}$, $I_D=4.8\text{A}$, $V_{GS}=0$ to 10V

¹⁾ $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 400V

²⁾ $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 400V

Table 9 Reverse diode characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode forward voltage	V_{SD}	-	0.9	-	V	$V_{GS}=0V$, $I_F=4.8A$, $T_j=25^{\circ}C$
Reverse recovery time	t_{rr}	-	232	-	ns	$V_R=400V$, $I_F=4.8A$, $di_F/dt=100A/\mu s$; see table 10
Reverse recovery charge	Q_{rr}	-	2.1	-	μC	$V_R=400V$, $I_F=4.8A$, $di_F/dt=100A/\mu s$; see table 10
Peak reverse recovery current	I_{rrm}	-	17	-	A	$V_R=400V$, $I_F=4.8A$, $di_F/dt=100A/\mu s$; see table 10

5 Electrical characteristics diagrams

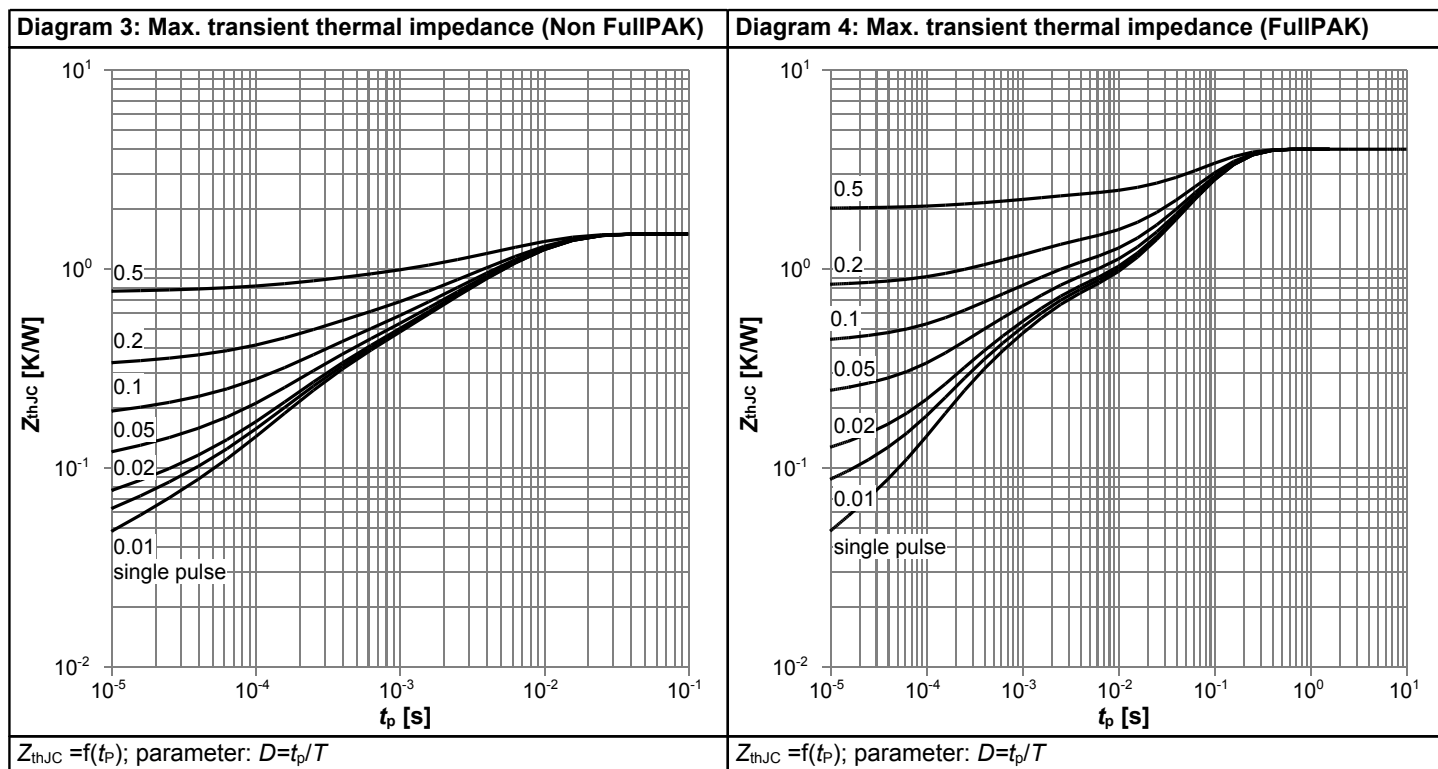
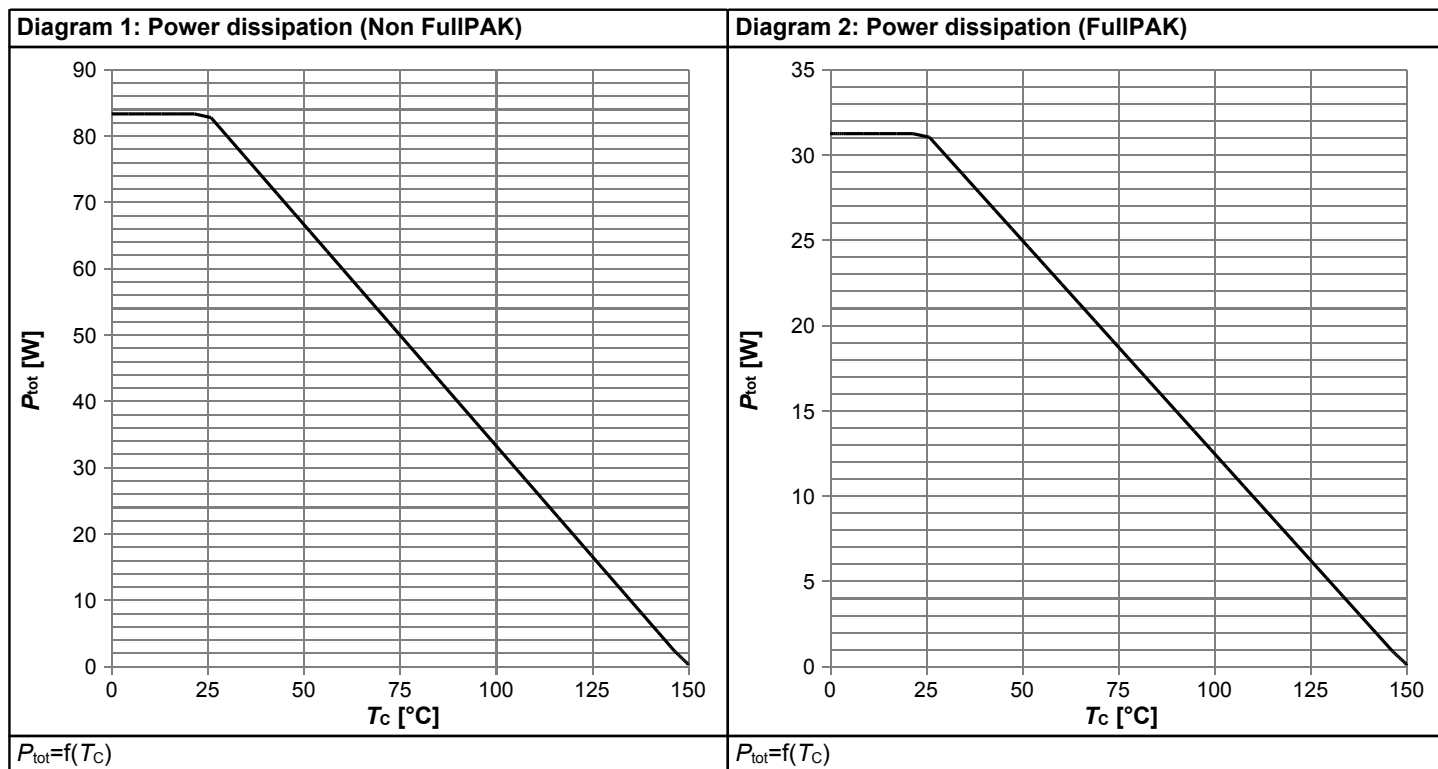
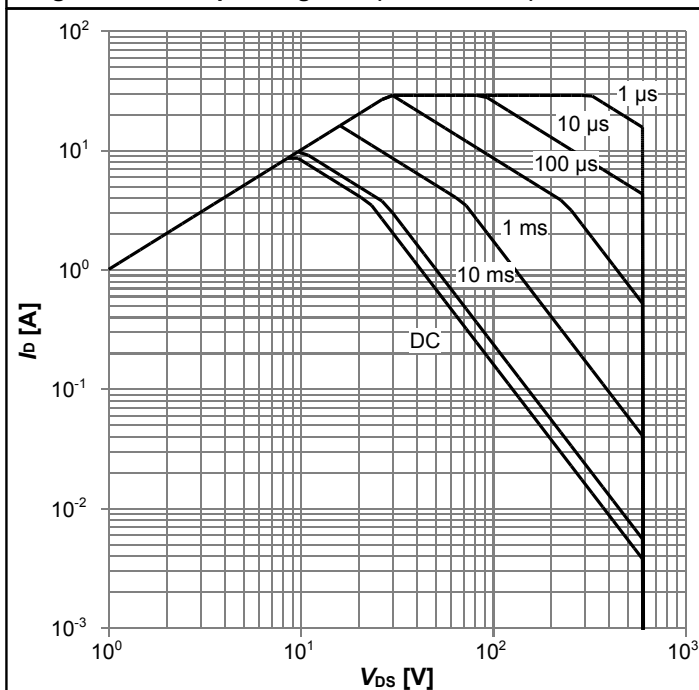
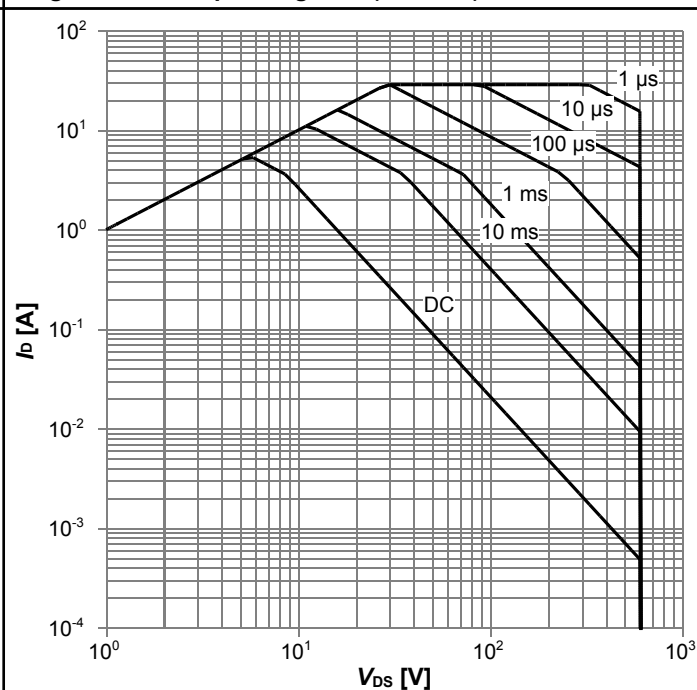


Diagram 5: Safe operating area (Non FullPAK)



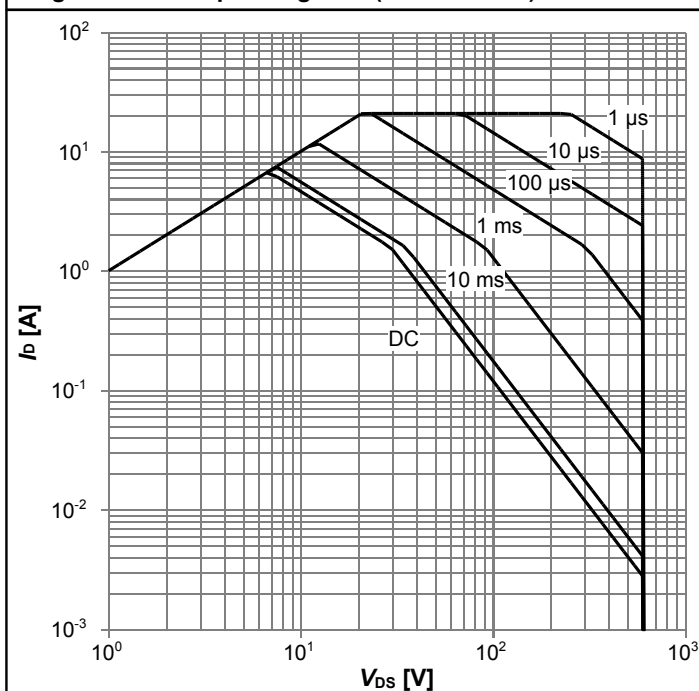
$I_D = f(V_{DS})$; $T_C = 25^\circ\text{C}$; $D = 0$; parameter: t_p

Diagram 6: Safe operating area (FullPAK)



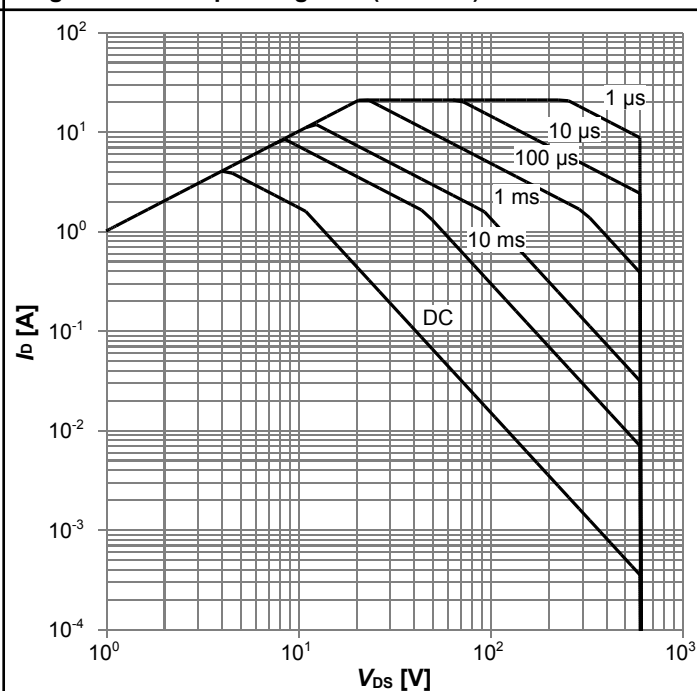
$I_D = f(V_{DS})$; $T_C = 25^\circ\text{C}$; $D = 0$; parameter: t_p

Diagram 7: Safe operating area (Non FullPAK)



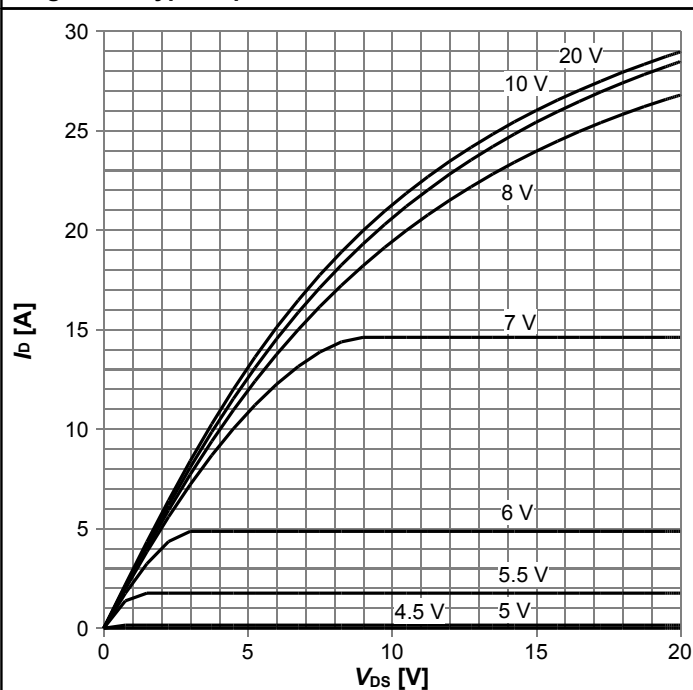
$I_D = f(V_{DS})$; $T_C = 80^\circ\text{C}$; $D = 0$; parameter: t_p

Diagram 8: Safe operating area (FullPAK)



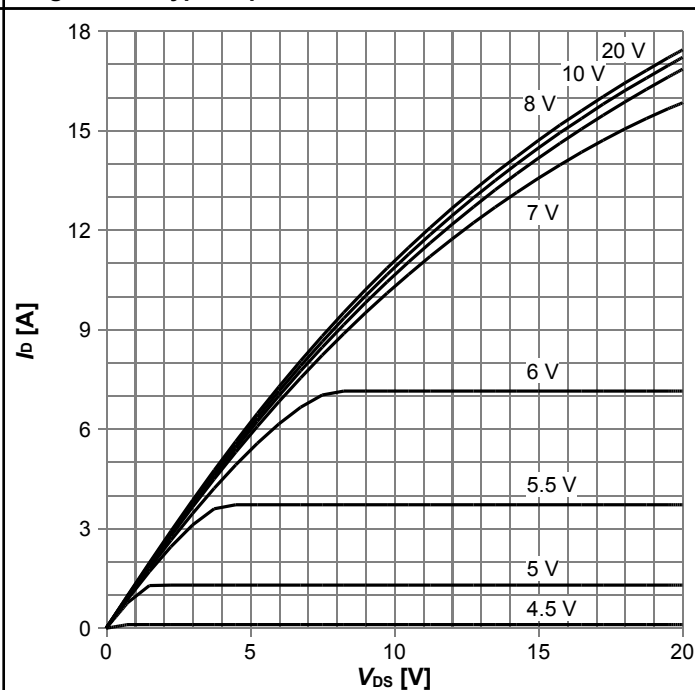
$I_D = f(V_{DS})$; $T_C = 80^\circ\text{C}$; $D = 0$; parameter: t_p

Diagram 9: Typ. output characteristics



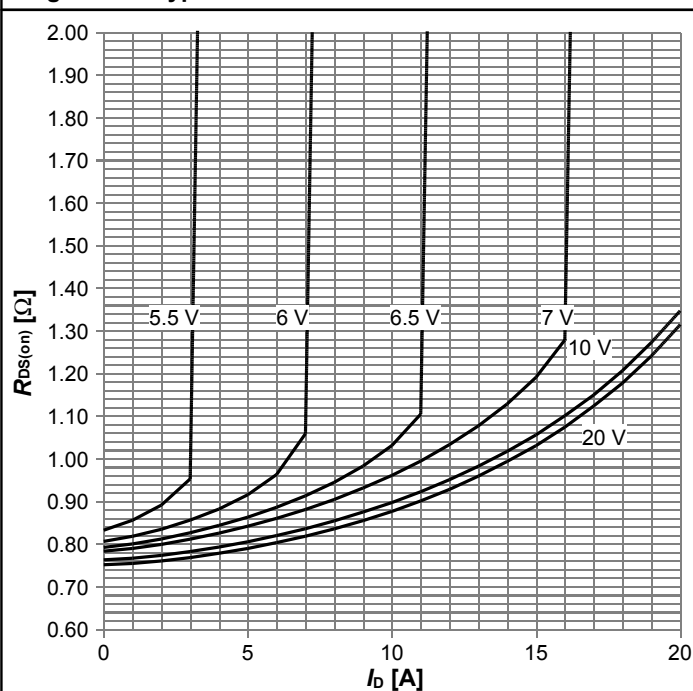
$I_D = f(V_{DS})$; $T_J = 25\text{ °C}$; parameter: V_{GS}

Diagram 10: Typ. output characteristics



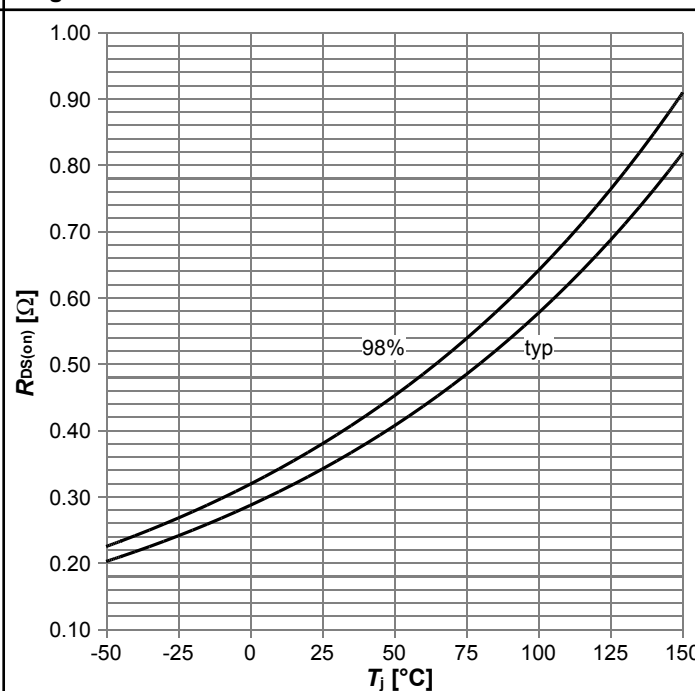
$I_D = f(V_{DS})$; $T_J = 125\text{ °C}$; parameter: V_{GS}

Diagram 11: Typ. drain-source on-state resistance



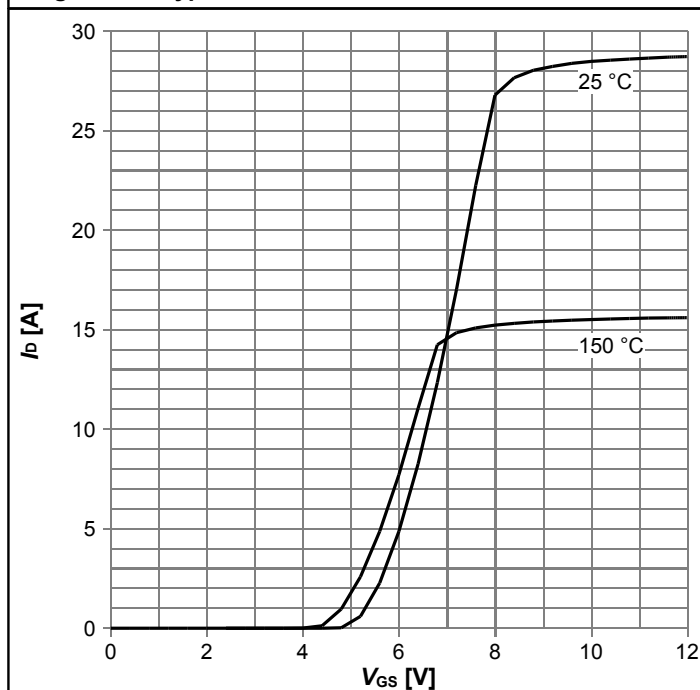
$R_{DS(on)} = f(I_D)$; $T_J = 125\text{ °C}$; parameter: V_{GS}

Diagram 12: Drain-source on-state resistance



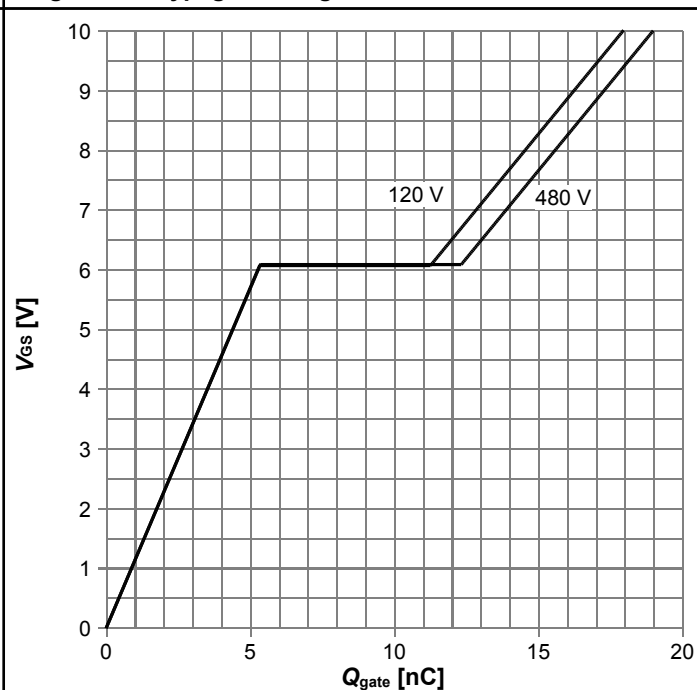
$R_{DS(on)} = f(T_J)$; $I_D = 3.8\text{ A}$; $V_{GS} = 10\text{ V}$

Diagram 13: Typ. transfer characteristics



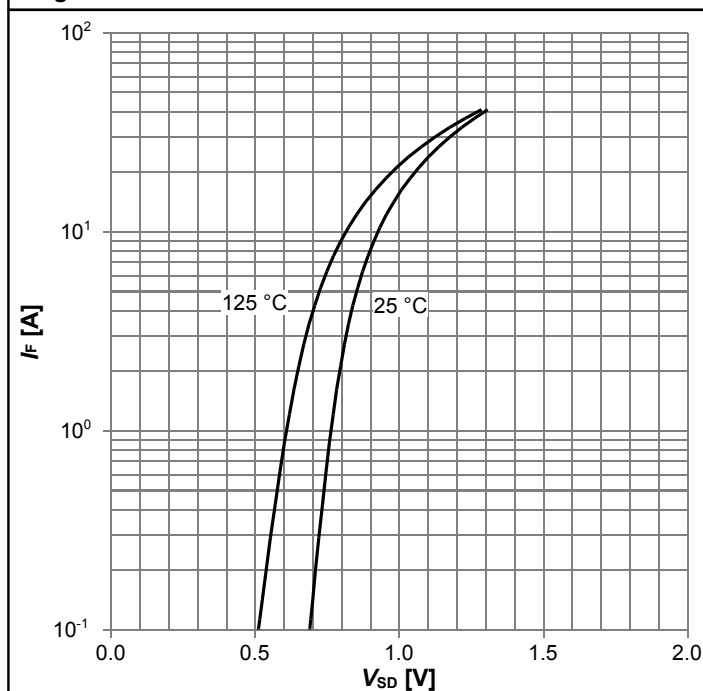
$I_D = f(V_{GS})$; $V_{DS} = 20V$; parameter: T_j

Diagram 14: Typ. gate charge



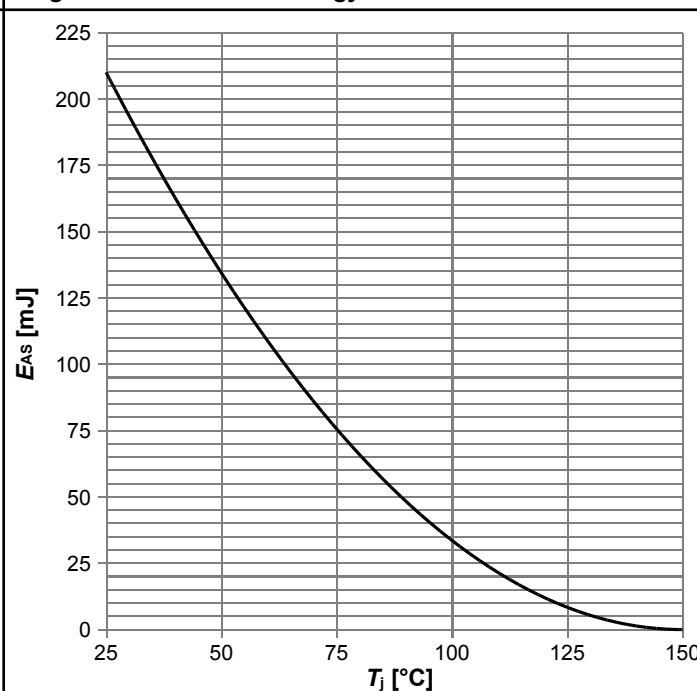
$V_{GS} = f(Q_{gate})$; $I_D = 4.8 A$ pulsed; parameter: V_{DD}

Diagram 15: Forward characteristics of reverse diode



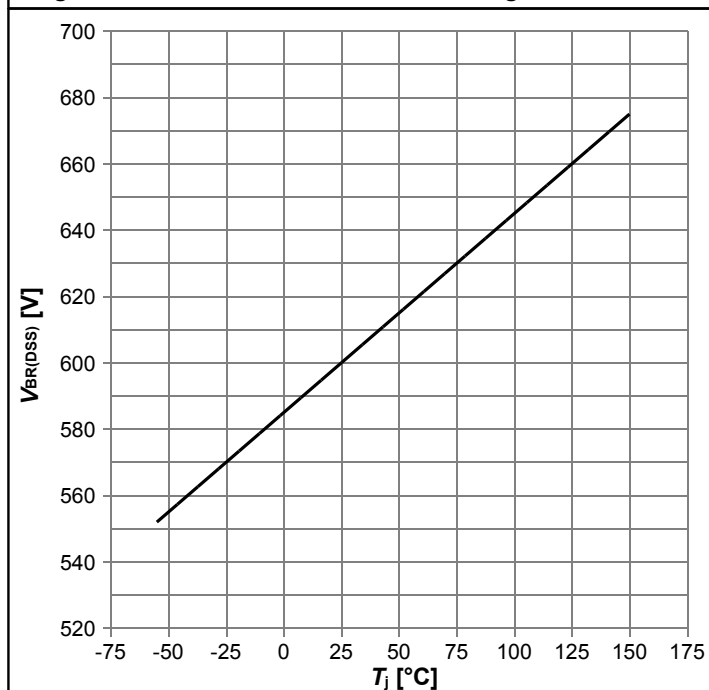
$I_F = f(V_{SD})$; parameter: T_j

Diagram 16: Avalanche energy



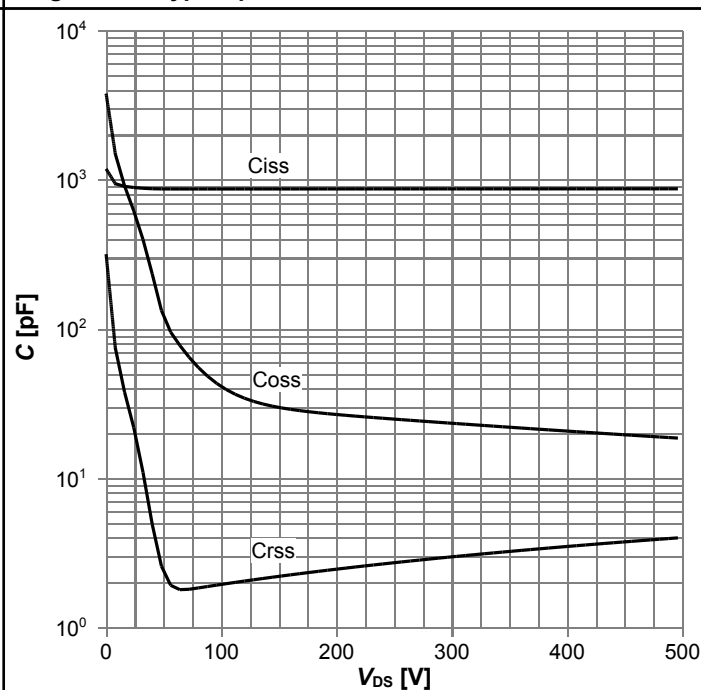
$E_{AS} = f(T_j)$; $I_D = 1.8 A$; $V_{DD} = 50 V$

Diagram 17: Drain-source breakdown voltage



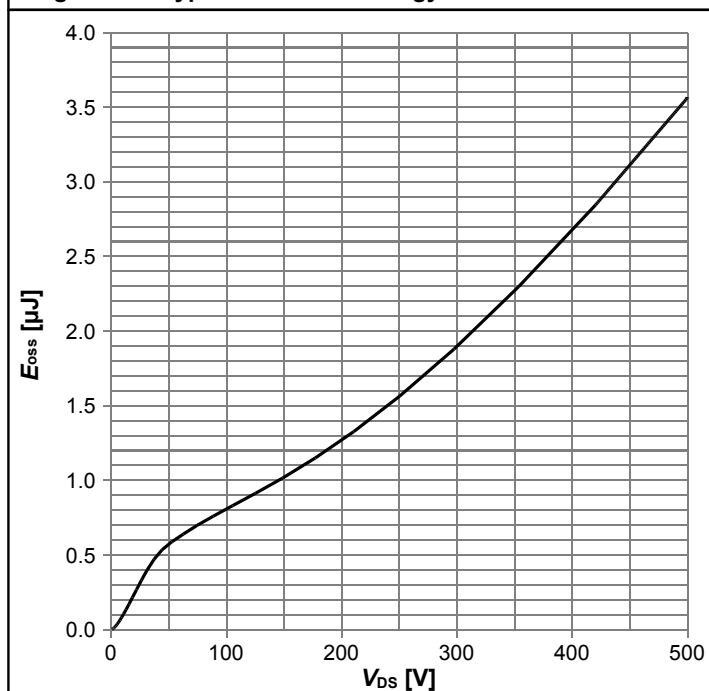
$$V_{BR(DSS)} = f(T_j); I_D = 1 \text{ mA}$$

Diagram 18: Typ. capacitances



$$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$$

Diagram 19: Typ. Coss stored energy



$$E_{oss} = f(V_{DS})$$

6 Test Circuits

Table 10 Diode characteristics

Test circuit for diode characteristics

$R_{g1} = R_{g2}$

Diode recovery waveform

$t_{rr} = t_F + t_S$
 $Q_{rr} = Q_F + Q_S$

Table 11 Switching times

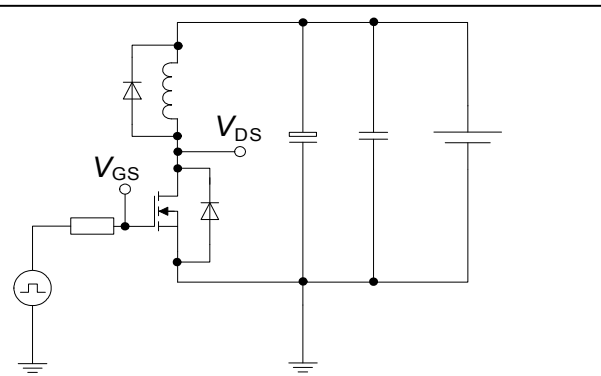
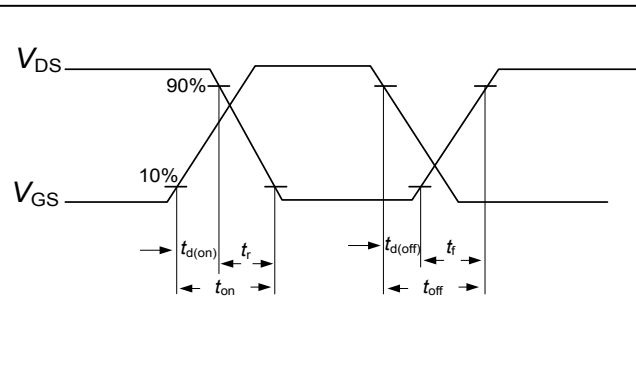
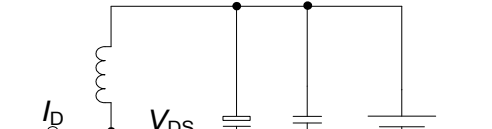
Switching times test circuit for inductive load	Switching times waveform
 The circuit diagram illustrates a switching test setup for an inductive load. A MOSFET is driven by a pulse generator connected to its gate through a resistor. The gate voltage is labeled V_{GS}. The MOSFET's drain is connected to a load consisting of an inductor and a capacitor in parallel, which is also connected to a freewheeling diode. The drain-source voltage is labeled V_{DS}.	 The timing diagram shows the switching waveforms for V_{DS} and V_{GS}. The gate voltage V_{GS} transitions from 10% to 90% during the turn-on phase, and the drain voltage V_{DS} transitions from 90% to 10% during the turn-off phase. The key switching parameters are labeled as follows: $t_{d(on)}$: Delay time from gate voltage rise to drain voltage fall. t_r: Rise time of the drain voltage. t_{on}: Total turn-on time. $t_{d(off)}$: Delay time from gate voltage fall to drain voltage rise. t_f: Fall time of the drain voltage. t_{off}: Total turn-off time.

Table 12 Unclamped inductive load

Unclamped inductive load test circuit	Unclamped inductive waveform
	

7 Package Outlines

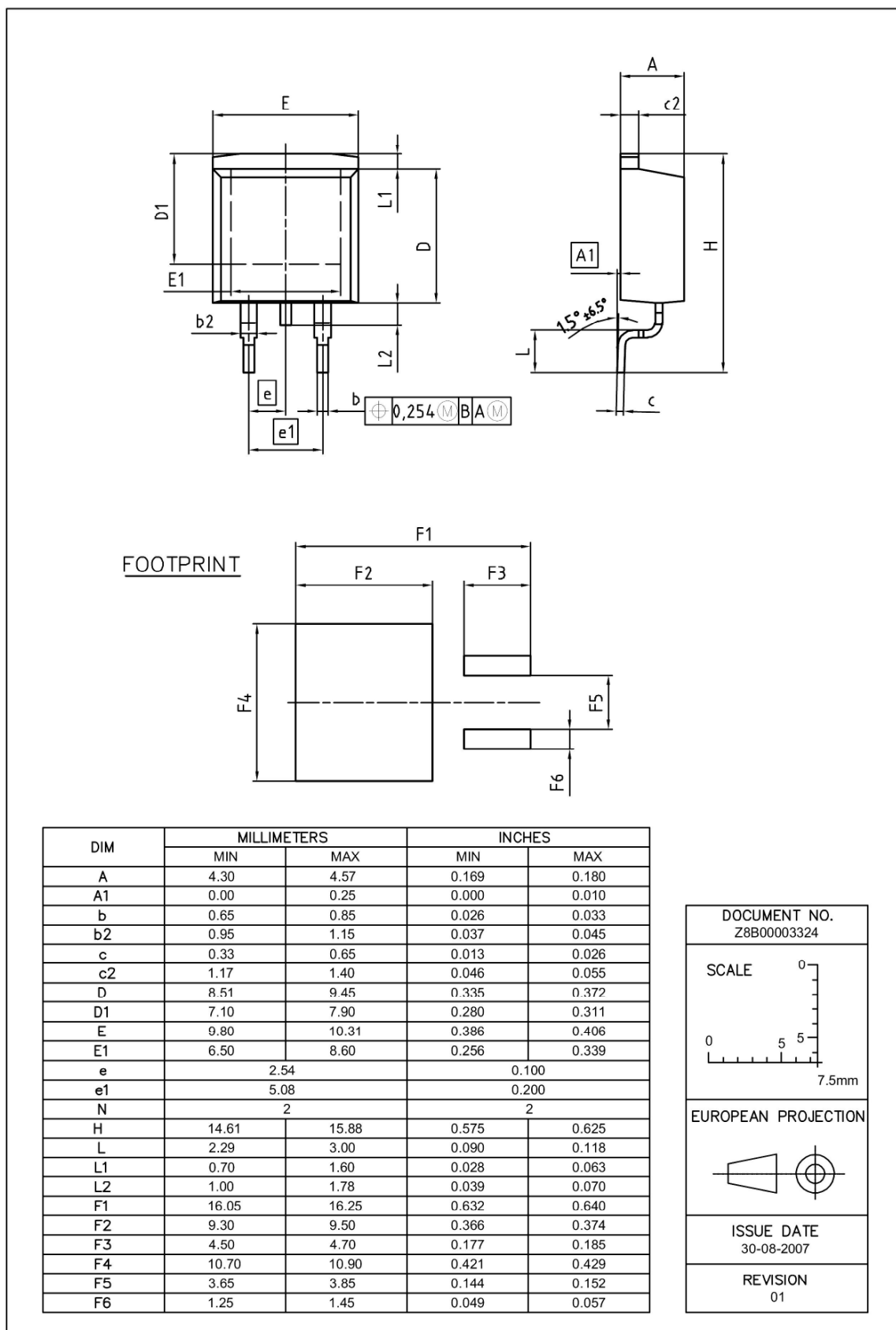


Figure 1 Outline PG-TO 263, dimensions in mm/inches

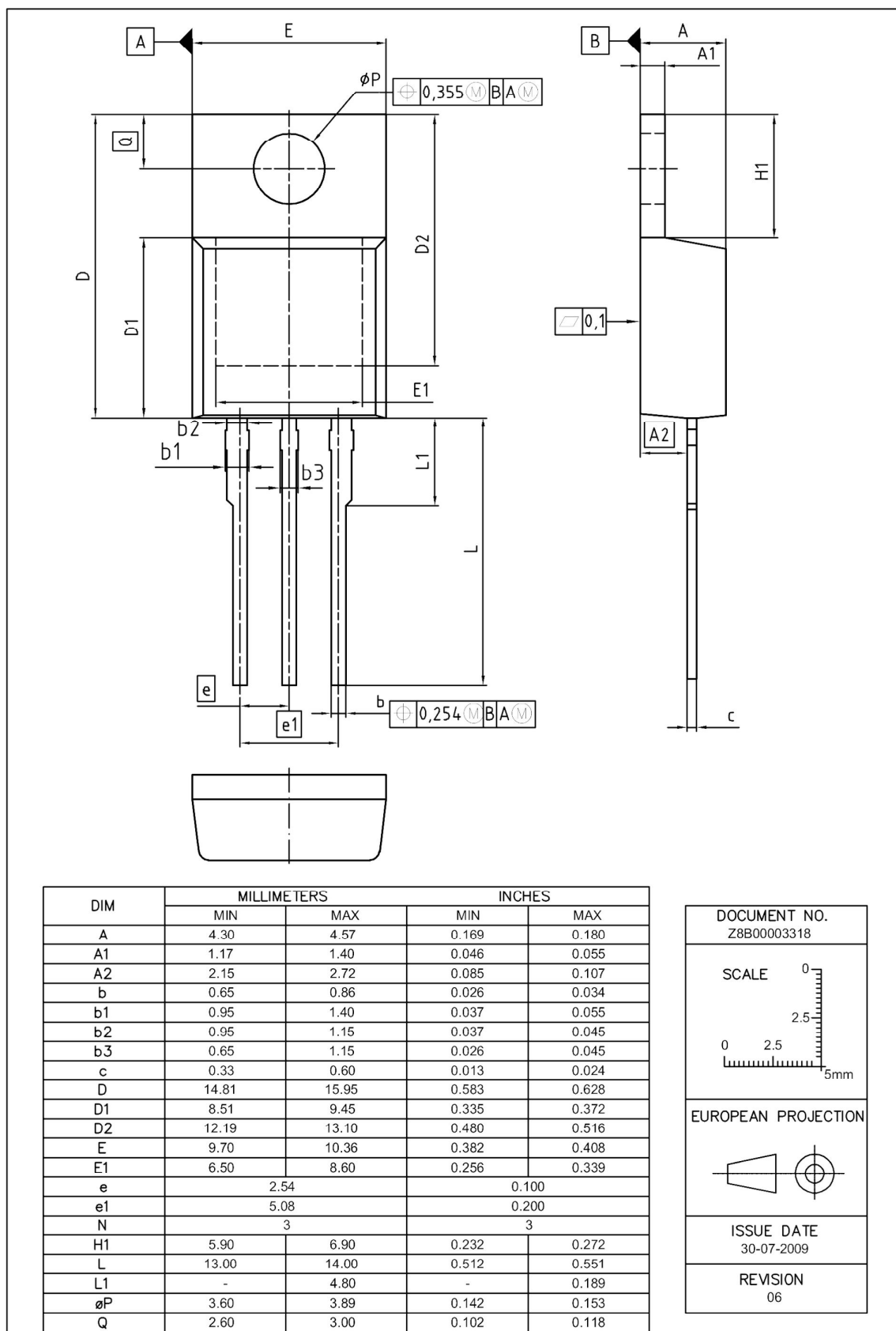
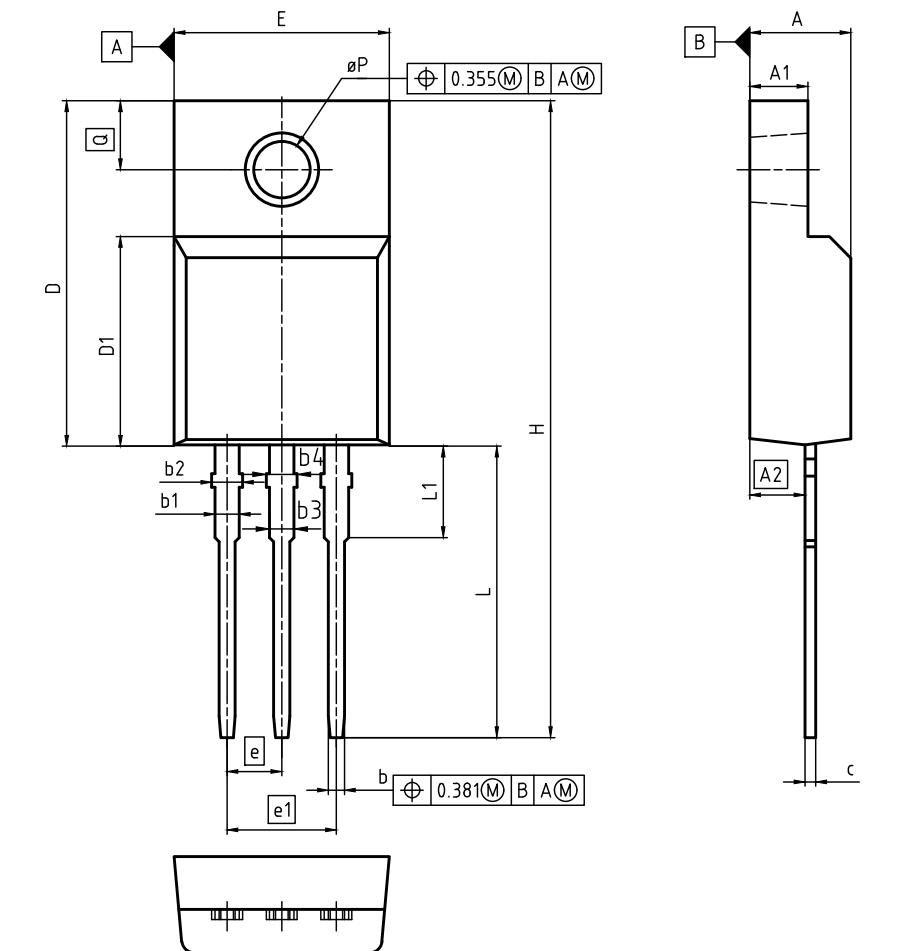


Figure 2 Outline PG-TO 220, dimensions in mm/inches



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.50	4.90	0.177	0.193
A1	2.34	2.85	0.092	0.112
A2	2.42	2.86	0.095	0.113
b	0.65	0.90	0.026	0.035
b1	0.95	1.38	0.037	0.054
b2	0.95	1.51	0.037	0.059
b3	0.65	1.38	0.026	0.054
b4	0.65	1.51	0.026	0.059
c	0.40	0.63	0.016	0.025
D	15.67	16.15	0.617	0.636
D1	8.97	9.83	0.353	0.387
E	10.00	10.65	0.394	0.419
e	2.54 (BSC)		0.100 (BSC)	
e1	5.08		0.200	
N	3		3	
H	28.70	29.75	1.130	1.171
L	12.78	13.75	0.503	0.541
L1	2.83	3.45	0.111	0.136
øP	2.95	3.38	0.116	0.133
Q	3.15	3.50	0.124	0.138

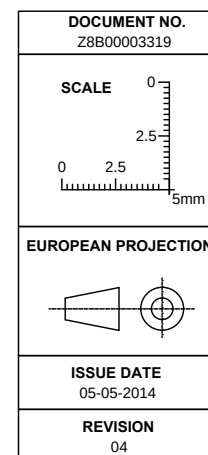


Figure 3 Outline PG-TO 220 FullIPAK, dimensions in mm/inches

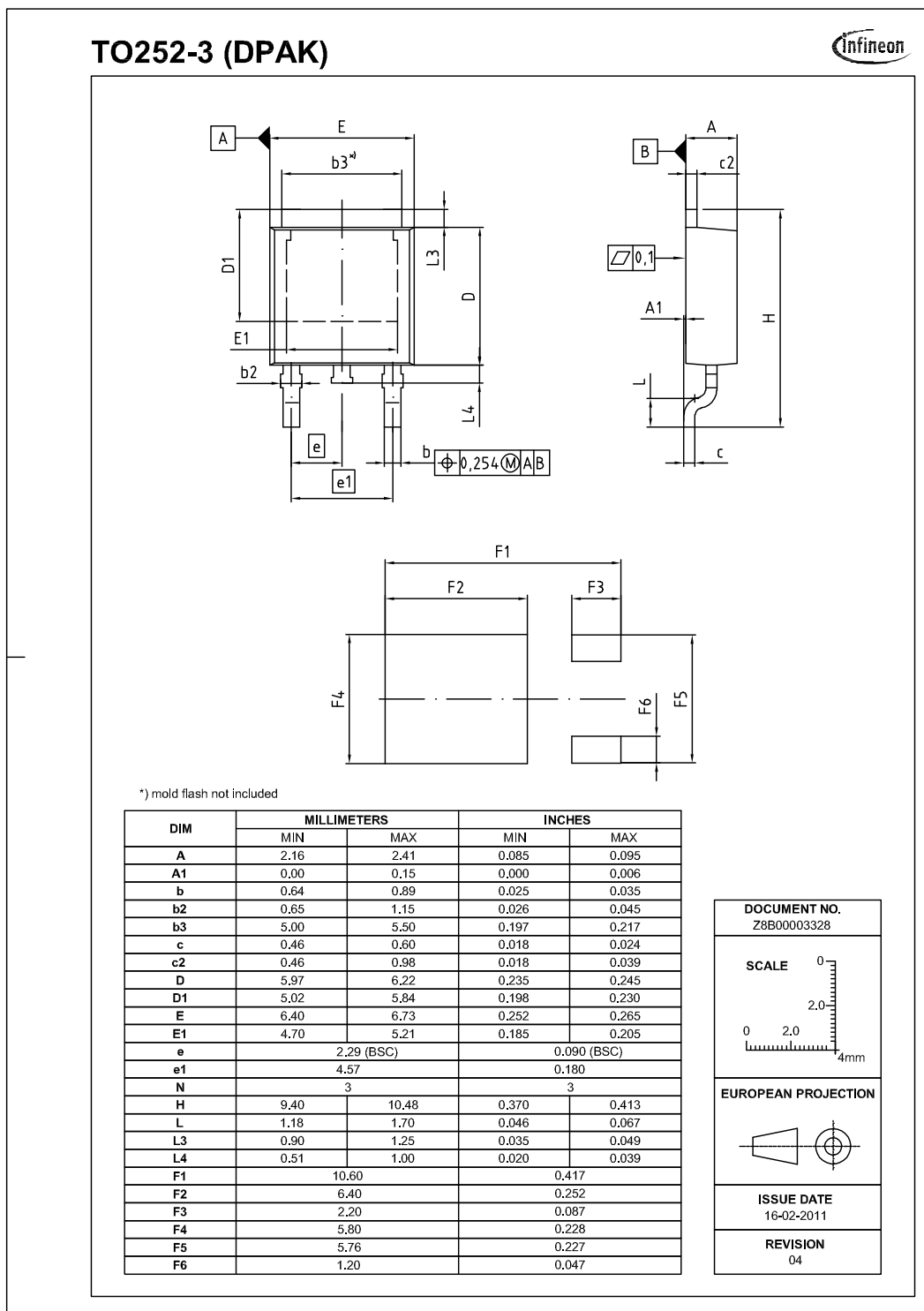


Figure 4 Outline PG-TO 252, dimensions in mm/inches

8 Appendix A

Table 13 Related Links

- IFX CoolMOS™ P6 Webpage: www.infineon.com
- IFX CoolMOS™ P6 application note: www.infineon.com
- IFX CoolMOS™ P6 simulation model: www.infineon.com
- IFX Design tools: www.infineon.com

Revision History

IPB60R380P6, IPP60R380P6, IPA60R380P6, IPD60R380P6

Revision: 2015-07-10, Rev. 2.2

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.0	2013-12-05	Release of final version
2.1	2013-12-05	Release of multi-package datasheet
2.2	2015-07-10	PG-TO 263 package added

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Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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